

MEMRISYS 2021 Monday November 1, 2021 Day 1 (1/3)

Japan Time

8:30-8:40	Opening Remarks Masakazu Aono National Institute for Materials Science, Tsukuba, Japan							
Honorary Session, Chair: Masakazu Aono								
8:45-9:30	HS-1	"Why Brains Need Memristors Blessed with An Edge of Chaos Kernel?" Leon Chua University of California Berkeley, Berkeley, USA						
Plenary Session 1, Chair: Wei Lu								
9:30-10:15	PS-1	"Dynamically Active Memristors at the 'Edge of Chaos': pulse amplification, computation and data transmission" Richard Stanley Williams Texas A&M University, Texas, USA						
10:15-10:25	Break							
Technical Session 1, Chair: Yiyang Li				Technical Session 2, Chair: Akihito Sawa				
10:25-10:50	1A-1	Keynote "Atomistic Simulations to Understand Microscopic Mechanism of Ion-Migration-based Resistive Switching Systems" Satoshi Watanabe The University of Tokyo, Tokyo, Japan			1B-1	Keynote "Nanowire Networks for Neuromorphic Dynamics" Tomonobu Nakayama National Institute for Materials Science, Tsukuba, Japan		
10:50-11:15	1A-2	Invited "Exploring Novel Functions at Solid/solid Electrolyte Interfaces for Neuromorphic Applications" Takashi Tsuchiya National Institute for Materials Science, Tsukuba, Japan			1B-2	Invited "Understanding the Interfaces of Solid Electrolytes and Electrodes for Memristive Devices" Taro Hitosugi Tokyo Institute of Technology, Tokyo, Japan		
11:15-11:30	1A-3	Construction of Neural Network Potential to Investigate Interface Structures of metal/Li ₃ PO ₄	Koji Shimizu	The University of Tokyo, Tokyo, Japan	1B-3	Demonstration of Memristor-based Spiking Neural Network	Wellington de Oliveira Avelino	Federal University of Minas Gerais, Belo Horizonte, Brazil
11:30-11:45	1A-4	Emulation of Synaptic Plasticity in Memristor Crossbar Arrays for Neuromorphic Applications	Haider Abbas	Hanyang University, Seoul, Republic of Korea	1B-4	Amorphous Metal-oxide Thin-film Memdevices and Integration to Neuromorphic Systems	Mutsumi Kimura	Ryukoku University, Kyoto, Japan
11:45-11:55	Break							
Technical Session 3, Chair: Qiangfei Xia				Technical Session 4, Chair: Munehiro Tada				
11:55-12:20	1A-5				1B-5	Invited "Investigation of Device Variation Impact and Complement Method for PCM-based Neuromorphic Computing" Akiyo Nomura IBM Research, Tokyo, Japan		
12:20-12:45	1A-6	Invited "Leaky-integrator Neuron for Sporadic Spike Inputs" Isao H. Inoue National Institute of Advanced Industrial Science and Technology, Tsukuba, Japan			1B-6	Invited "Power-free Synaptic Transistor" Teruo Kanki Osaka University, Osaka, Japan		

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12:45-13:00	1A-7	Low-Energy-Consumption Memory Device Inspired by All-Solid-State Li Batteries	Yuki Watanabe	Tokyo Institute of Technology, Tokyo, Japan	1B-7	Polarity independent resistive switching in MoS ₂ nanosheets and PEO based nanocomposite films	Rajesh Deb	National Institute of Technology Silchar, Silchar, India
13:00-13:15	1A-8	Digital and Analog Resistive Switching in NiO-based Memristor by Electrode Engineering	Swathi S. P.	Centre for Nano and Soft Matter Sciences, Bengaluru, India	1B-8	Role of Resistive Layer in Threshold-Memory Switching Memristor Device	Mari S. Yadav	Indian Institute of Technology Ropar, Punjab, India
13:15-14:00	Break							
14:00-15:45	Poster Session 1							
Technical Session 5, Chair: Teruo Kanki				Technical Session 6, Chair: Yusuke Nishi				
16:00-16:15	1A-9	Controlled Stochasticity in Nanoscale Phase Change Memory Devices	Laszlo Posa	Budapest University of Technology and Economics, Budapest, Hungary	1B-9	Optimized Programming Algorithms for Reliable Multi-Level Operation in 1T1R-based RRAM Arrays	Eduardo Perez	IHP-Leibniz-Institut für Innovative Mikroelektronik, Frankfurt, Germany
16:15-16:30	1A-10	Temperature Effect on the Switching Characteristic of Diffusive Memristor	Debi P. Pattnaik	Loughborough University, Loughborough, UK	1B-10	A Systematic Approach for Designing Robust Bio-Inspired Memristive Circuits	Alon Ascoli	Technische Universität Dresden, Dresden, Germany
16:30-16:45	1A-11	A Tunable CMOS-Memristor Delay Element	Jiawei Shen	Imperial College London, London, UK	1B-11	Modelling Memristor Arrays with Passive Selectors – A MATLAB Tool	Yasir J. Noori	University of Southampton, Southampton, UK
16:45-16:55	Break							
Technical Session 7, Chair: Themis Prodromakis				Technical Session 8, Chair: Georgios Sirakoulis				
16:55-17:20	1A-12	Invited "On-chip Inference and Training Based on Memristive Device Elements" Yuchao Yang Peking University, Beijing, China			1B-12	Invited "Subfilamentary Networks and Their Dynamics as Source of Cycle-to-cycle Variability in ReRAM Devices" Regina Dittmann Forschungszentrum Jülich GmbH, Jülich, Germany		
17:20-17:45	1A-13	Keynote "In-memory Computing with Memristive Devices for Machine Learning and Broader Applications" John Paul Strachan Forschungszentrum Jülich GmbH, Jülich, Germany			1B-13	Keynote "New Insights into Memristor Dynamics: Model Predictions Verified by Experiments" Ronald Tetzlaff Technische Universität Dresden, Dresden, Germany		
17:45-18:10	1A-14	Keynote "Material Learning with Disordered Dopant Networks" Wilfred G. van der Wiel University of Twente, Enschede, The Netherlands			1B-14	Keynote "Utilizing the Concept of Complementary Resistive Switches for Neuromorphic Computing" Rainer Waser RWTH Aachen University, Aachen, Germany		
18:10-18:20	Break							

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18:20-19:05	PS-2	<p data-bbox="1070 180 1411 204">Plenary Session 2, Chair: Paolo Milani</p> <p data-bbox="1061 233 1420 256">"Computational Phase-change Memory"</p> <p data-bbox="1151 263 1330 287">Evangelos Elefteriou</p> <p data-bbox="1111 293 1370 317">Axelera AI, Zurich, Switzerland</p>
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MEMRISYS 2021 Tuesday November 2, 2021 Day 2 (1/2)

Japan Time

7:00-7:30	International Steering Committee Meeting							
	Technical Session 9, Chair: Tomonobu Nakayama				Technical Session 10, Chair: Chair: Isao Inoue			
9:00-9:25	2A-1	Keynote "In-materio Computation" James K. Gimzewski University of California, Los Angeles, Los Angeles, USA			2B-1	Keynote "Modular Memristive Crossbar Architectures and Dynamic Memristive Networks" Wei Lu University of Michigan, Ann Arbor, USA		
9:25-9:50	2A-2	Invited "Towards Physical Neuromorphic Device Consisting of Nanomaterials" Megumi Akai-Kasaya Osaka University, Osaka, Japan			2B-2	Keynote "A Single Device Neuristor which Exhibits Neuronal Functionalities" Ivan Schuller University of California San Diego, San Diego, USA		
9:50-10:15	2A-3	Invited "In-Materio Computing Devices Consisted of Random Network Nanoparticles for Autonomous robotics" Hirofumi Tanaka Kyushu Institute of Technology, Fukuoka, Japan			2B-3	Invited "Material Strategies for Memristor-based AI Hardware and Their Heterointegration" Jeehwan Kim Massachusetts Institute of Technology, Massachusetts, USA		
10:15-10:25	Break							
	Plenary Session 3, Chair: Tsuyoshi Hasegawa							
10:25-11:10	PS-3	"Memristive Dynamics Enabled Hardware Elements and Circuits for Neuromorphic Computing" Ru Huang Peking University, Beijing, China						
11:10-11:20	Break							
	Technical Session 11, Chair: Masashi Arita				Technical Session 12, Chair: Megumi Akai-Kasaya			
11:20-11:45	2A-4	Invited "Current Status and Issues of In-memory Accelerators for Deep Neural Networks" Jun Deguchi Kioxia Corporation, Tokyo, Japan			2B-4	Invited "Amoeba-inspired Combinatorial Optimization Machines Fusing Digital and Analog" Masashi Aono Amoeba Energy Co., Ltd., Yokohama, Japan		
11:45-12:00	2A-5	Complementary Resistive Switching Characteristics and Gradual Set/Reset Processes in Pt/TaO _x /Ta ₂ O ₅ /Pt Cells	Toshiki Miyatani	Kyoto University, Kyoto, Japan	2B-5	Emulating Retinal Receptive Field by Li-ion-based Neuromorphic System	Xiang Wan	National Institute for Materials Science, Tsukuba, Japan
12:00-12:15	2A-6	A Bio-electronic Memristive Interface for Real-time Coupling of Neuronal Populations	Catarina Dias	University of Porto, Porto, Portugal	2B-6	Simulation of Memristor Switching Time Series in Response to Spike-like Signal	F. Meshchaninov	Moscow Institute of Physics and Technology, Moscow, Russia
12:15-13:30	Break							
13:30-15:45	Poster Session 2							

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		Technical Session 13, Chair: Hirofumi Tanaka			Technical Session 14, Chair: Yuchao Yang		
16:00-16:15	2A-7	Nanosecond Resistive Switching in Ag/AgI/PtIr Nanojunctions	Daniel Molnar	Budapest University of Technology and Economics, Budapest, Hungary	2B-7	Investigation of Resistive Switching with Numerical Simulations	Christiane Ader RWTH Aachen University, Aachen, Germany
16:15-16:30	2A-8	Activity- and Noise-controlled Resistive Switching in Metal-oxide Devices	Alexey Mikhaylov	Lobachevsky University, Nizhny Novgorod, Russia	2B-8	An Axisymmetric 2D Simulation Model for the SET Kinetics of Electrochemical Metallization Cells	Milan Buttberg RWTH Aachen University, Aachen, Germany
16:30-16:45	2A-9	Point Defect and Grain Boundary Engineering in Metal Oxide Valence Change Type Memristive Devices	Lambert Alff	Technische Universität Darmstadt, Darmstadt, Germany	2B-9	Pattern Formation in Memristor Cellular Nonlinear Networks Operating in the Edge of Chaos	Angela Slavova Bulgarian Academy of Sciences, Sofia, Bulgaria
16:45-16:55	Break						
		Technical Session 15, Chair: Xin Guo			Technical Session 16 Chair: Daniele Ielmini		
16:55-17:20	2A-10	Invited "Nanowire Memristor: From Single Device to Self-organized Networks" Carlo Ricciardi Politecnico di Torino, Torino, Italy			2B-10	Keynote "In-memory Computing with Memristors" Xiangshui Miao Huazhong University of Science and Technology, Wuhan, China	
17:20-17:45	2A-11	Invited "Effect of Au Electrode on the Resistance Change Response of HfO _x -based ReRAM Device under Voltage Pulse Trains" Shoso Shingubara Kansai University, Osaka, Japan			2B-11	Keynote "Wave Computing with Memristive Oscillatory Systems" Georgios. Ch. Sirakoulis Democritus University of Thrace, Xanthi, Greece	
17:45-18:10	2A-12	Keynote "Influence of Impurities in Electrode Materials on the Memristive Characteristics of ECM Devices" Iliia Valov Forschungszentrum Jülich GmbH, Jülich, Germany			2B-12	Keynote "A Novel Reservoir Computing Model for Memristive Device Arrays" Tetsuya Asai Hokkaido University, Sapporo, Japan	
18:10-18:20	Break						
Plenary Session 4, Chair: Huaqiang Wu							
18:20-19:05	PS-4	"Environmental Effects in RRAM - Tools, Models, and Applications" Themis Prodromakis University of Southampton, Southampton, UK.					

MEMRISYS 2021 Wednesday November 3, 2021 Day 3 (1/2)

Japan Time

Plenary Session 5, Chair: Toshitsugu Sakamoto								
9:00-9:45	PS-5	<p style="text-align: center;">"Via-switch FPGA with Transistor-free Programmability Enabling Near-Memory Parallel Computation" Masanori Hashimoto Kyoto University, Kyoto, Japan</p>						
9:45-9:55	Break							
Technical Session 17, Chair: Shoso Shingubara				Technical Session 18, Chair: Joshua Yang				
9:55-10:20	3A-1	<p style="text-align: center;">Keynote "Radiation-tolerant Atom-switch FPGA" Toshitsugu Sakamoto NanoBridge Semiconductor, Inc., Tsukuba, Japan</p>			3B-1	<p style="text-align: center;">Keynote "Developing Fully Hardware Implemented Computation-in-Memristor System" Huaqiang Wu Tsinghua University, Beijing, China</p>		
10:20-10:45	3A-2	<p style="text-align: center;">Invited "Linear & Deterministic Analog Resistive Memory Using Three-terminal Valence-change Memory" Yiyang Li University of Michigan, Ann Arbor, USA</p>			3B-2	<p style="text-align: center;">Keynote "Artificial Olfactory System" Xin Guo Huazhong University of Science and Technology, Wuhan, China</p>		
10:45-11:00	3A-3	Flexible Resistance Modulation on a SmNiO ₃ Chemical Transistor	Azusa N. Hattori	Osaka University, Osaka, Japan	3B-3	In situ Manipulation of Magnetic Anisotropy in Magnetite Thin Film, Achieved with an All-solid-state Redox Device	Wataru Namiki	National Institute for Materials Science, Tsukuba, Japan
11:00-11:10	Break							
Technical Session 19, Chair: Takashi Tsuchiya				Technical Session 20, Chair: Katsunori Makihara				
11:10-11:25	3A-4	Operando Observation of Analog Resistance Change in Buried Metal/Oxide Interface	Hisashi Shima	National Institute of Advanced Industrial Science and Technology, Tsukuba, Japan	3B-4	C-N-codoped Sb ₂ Te ₃ Chalcogenides for High-performance Phase-change Devices	You Yin	Gunma University, Gunma, Japan
11:25-11:40	3A-5	Reduction of Initial Reset Voltages in Resistive Switching Cells with a Ti/Pr _{0.7} Ca _{0.3} MnO _x Interface	Makoto Imuro	Kyoto University, Kyoto, Japan	3B-5	Cu Movement in MoO _x /Al ₂ O ₃ Double Layer CBRAM Studied by In-situ TEM	Masashi Arita	Hokkaido University, Sapporo, Japan
11:40-11:55	3A-6	Nanoclusters Formation Dynamics Dominated by Dipolar Ionic Diffusion and Reversible Nucleation	Fei Zeng	Tsinghua University, Beijing, China	3B-6	Dynamics of Electric Field-Assisted Hydrogenation in Proton-Doped NdNiO ₃ Thin Film Resistors	Umar Sidik	Osaka University, Osaka, Japan
11:55-13:30	Break							
13:30-15:45	Poster Session 3							
Technical Session 21, Chair: Regina Dittmann				Technical Session 22, Chair: Marina Yamaguchi				
16:00-16:25	3A-7	<p style="text-align: center;">Invited "Natural Intelligence in Colloidal Particle Systems with Memory Effects" Toshiharu Saiki Keio University, Yokohama, Japan</p>			3B-7	<p style="text-align: center;">Invited "Spatiotemporal Information Processing with Oxide-based Electrolyte-Gated Transistors" Da-Shan Shang Institute of Microelectronics (IME), CAS, China</p>		

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16:25-16:40	3A-8	Noise-induced and Self-sustained Current Spiking Regimes in a NbO _x Thin Film Device	Ben A. Johnson	Loughborough University, Loughborough, UK	3B-8	Microscopic Origin of the Analog and Symmetric Conductance Update in MO _x /HfO ₂ RRAM	Valeria Bragaglia	IBM Research - Zurich, Rüschlikon, Switzerland
16:40-16:55	3A-9	Improved Weight Update Linearity through Engineered Domain Dynamics in Ferroelectric Tunnel Junctions	Sayani Majumdar	VTT Technical Research Centre of Finland, Otaniemi, Finland	3B-9	Gate-Enabled Operation Point Tuning in an Atomic-Scale Memristor	Mila Lewerenz	ETH Zurich, Zurich, Switzerland
16:55-17:10	3A-10	Second-order Spike-timing-dependent-plasticity of Parylene-based Memristors	A.N. Matsukatova	National Research Center "Kurchatov Institute", Moscow, Russia	3B-10	A Back-end, CMOS Compatible Ferroelectric Field Effect Transistor for Synaptic Weights	Laura Begon-Lours	IBM Research-Zurich, Zurich, Switzerland
17:10-17:20	Break							
Technical Session 23, Chair: John Paul Strachan				Technical Session 24, Chair: Satoshi Watanabe				
17:20-17:35	3A-11	Memristive Synapses Connect Brain and Silicon Spiking Neurons	Alexantrou Serb	University of Southampton, Southampton, UK	3B-11	Physics-based Modeling of HRS Instability and Retention Phenomena in Filamentary VCM ReRAM	Nils Kopperberg	RWTH Aachen University, Aachen, Germany
17:35-17:50	3A-12	In-depth Characterization of Switching Dynamics in Amorphous HfO ₂ Memristive Arrays for the Implementation of Stochastic Learning Rules	Eduardo Perez	IHP-Leibniz-Institut für Innovative Mikroelektronik, Frankfurt, Germany	3B-12	Accurate Description of the Electronic Conduction at Interfaces in Compact Models	Christopher Bengel	RWTH Aachen University, Aachen, Germany
17:50-18:05	3A-13	In situ TEM Observation of Grain Growth in Textured HfO ₂ Based Memristors	Robert Eilhardt	Technical University of Darmstadt, Darmstadt, Germany	3B-13	A Compact Stochastic Model for Non-filamentary Memristive Devices	Sahitya Yarragolla	Ruhr University Bochum, Bochum, Germany
18:05-18:30	3A-14	Keynote "A Binary Classifier Based on a Reconfigurable Dense Network of Metallic Nanojunctions" Paolo Milani University of Milano, Milano, Italy			3B-14	Invited "Reliability Modelling of Memristive Devices based on the Valence Change Mechanism" Stephan Menzel Forschungszentrum Jülich, Jülich, Germany		
18:30-18:40	Break							
Special Session 1 (Publisher), Chair: Ilia Valov								
18:40-19:10	SS-1	Editorial panel and discussion from IOP, Nature and Wiley						

MEMRISYS 2021 Thursday November 4, 2021 Day 4 (1/2)

Japan Time

Special Session 2 (IRDS), Chair: Hiroyuki Akinaga									
9:00-9:30	SS-2	"Beyond-CMOS Roadmap - from Boolean Logic to Neuro-Inspired Computing" An Chen IBM Research, USA							
9:30-9:40	Break								
	Technical Session 25, Chair: Cheol Seong Hwang				Technical Session 26, Chair: Yoshifumi Nishi				
9:40-10:05	4A-1	Keynote "Resistive Switching and Neuromorphic Applications of Ferroelectric Tunnel Junctions" Akihito Sawa National Institute of Advanced Industrial Science and Technology, Tsukuba, Japan			4B-1	Keynote "Timing Selector: Using Transient Switching Dynamics to Solve the Sneak Path Issue of Crossbar Arrays" J. Joshua Yang University of Southern California, Los Angeles, USA			
10:05-10:30	4A-2	Invited "Electrode/Nb-doped SrTiO₃ junction as a physical reservoir device" Kentarō Kinoshita Tokyo University of Science, Tokyo, Japan			4B-2	Keynote "From Memristors to Memristive Neural Networks" Qiangfei Xia University of Massachusetts Amherst, Amherst, USA			
10:30-10:55	4A-3	Invited "Memristive Synapses and Neurons for Bioinspired Computing" Rui Yang Huazhong University of Science and Technology, Wuhan, China			4B-3	Invited "Optimal Data-splitting in RRAM-based Deep Learning Accelerators" Doo Seok Jeong Hanyang University, Seoul, Republic of Korea			
10:55-11:10	4A-4	Ferroelectric HfO ₂ -Based Monolayer MoS ₂ Optical Synaptic Transistor for Neuromorphic Vision Systems	Roda Nur	The University of Tokyo, Tokyo, Japan	4B-4	Building Binary CNN Accelerator with Fine Grain Memristor Crossbars	Changlin Chen	National University of Defense Technology, Changsha, China	
11:10-11:20	Break								
	Technical Session 27, Chair: Azusa N. Hattori				Technical Session 28, Chair: Kentaro Kinoshita				
11:20-11:35	4A-5	Optically-controllable Synaptic Characters of Vertically Aligned Graphene/Diamond Junctions	Kenji Ueda	Nagoya University, Nagoya, Japan	4B-5	Habituation and Sensitization Properties Mimicked in Four-terminal TiO _{2-x} Memristive Devices	Kenta Adachi	Osaka University, Osaka, Japan	
11:35-11:50	4A-6	A New Opportunity for the Emerging Tellurium Semiconductor: Making Resistive Switching Devices	Yifei Yang	Tsinghua University, Beijing, China	4B-6	Role of Nonlinearity in Memristive Networks for Reservoir Computing	Gouhei Tanaka	The University of Tokyo, Tokyo, Japan	
11:50-12:05	4A-7	Development of Physical Reservoir Devices Utilized Redox Reactions of Cu and Ag Ions in Ionic Liquids	Dan Sato	Tokyo University of Science, Tokyo, Japan	4B-7	3D Neuromorphic System Using Memristor Neuron and Fully Depleted Silicon-on-insulator Field Effect Transistor Synapse Devices	Yu-Rim Jeon	Hanyang University, Seoul, Republic of Korea	
12:05-12:20	4A-8	Conductance Control of Free-wiring Conductive Polymer Synapses	Naruki Hagiwara	Hokkaido University, Sapporo, Japan	4B-8	Controlling Retention Characteristics by Post-Annealing in Perovskite-Type Resistive Random Access Memory	Hiromasa Aoki	Tokyo University of Science, Tokyo, Japan	
12:20-13:30	Break								

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13:30-15:45	Poster Session 4							
16:00-16:45	Plenary Session 6, Chair: Taro Hitosugi							
	PS-6	"Ionic Nanoarchitectonics for Exploring Memristive Characteristics" Kazuya Terabe National Institute for Materials Science, Tsukuba, Japan						
16:45-16:55	Break							
	Technical Session 29, Chair: Stephan Menzel				Technical Session 30, Chair: Wilfred G. van der Wiel			
16:55-17:20	4A-9	Keynote "Solving Linear Algebra Problems with Analogue Closed-loop Memristive Circuits" Daniele Ielmini Politecnico di Milano, Milano, Italy			4B-9	Keynote "Time-varying Data Processing with Nonvolatile Memristor-based Temporal" Cheol Seong Hwang Seoul National University, Seoul, Republic of Korea		
17:20-17:35	4A-10	Conductive Filament Stabilization in Oxygen Engineered Hafnium and Yttrium Oxide-based RRAM Devices Revealed by Low-frequency Noise Studies	Eszter Piros	Technical University of Darmstadt, Darmstadt, Germany	4B-10	Noise Tailoring in Memristive Filaments	András Halbritter	Budapest University of Technology and Economics, Budapest, Hungary
17:35-17:50	4A-11	Voltage-time Dilemma of Current-driven Silver Single-atom Resistive Switches	Anna Nyary	Budapest University of Technology and Economics, Budapest, Hungary	4B-11	In-situ Soft and Hard X-ray Photoelectron Spectroscopy of Interface-based Resistive Switching in HfO ₂ -based Memristive Devices	Finn Zahari	Kiel University, Kiel, Germany
17:50-18:00	Break							
	Technical Session 31, Chair: Doo Seok Jeong				Technical Session 32, Chair: Rui Yang			
18:00-18:15	4A-12	Superconducting Subgap Spectroscopy of Transition Metal Oxide Memristors	Timea Nora Torok	Budapest University of Technology and Economics, Budapest, Hungary	4B-12	La ₂ NiO _{4+δ} -based Analog Memristive Devices for Artificial Synapse Applications	Khanh Khuu	University Grenoble Alpes, Grenoble, France
18:15-18:30	4A-13	SPIICE Model for Monomode Quantum Point Contact Memristors	Enrique A. Miranda	Universitat Autònoma de Barcelona, Barcelona, Spain	4B-13	Influence of the Dopant Concentration on ReRAM Electrochemical Properties	Carsten Weber	Research Center Jülich, Jülich, Germany
18:30-18:45	4A-14	Silicon Oxide ReRAM and System-level Solutions to Deal with Device Non-idealities for Better Inference Accuracy	Adnan Mehonic	University College London, London, UK	4B-14	Deterministic Modeling to Understand Effects of Noise in Diffusive Memristors	Yury Ushakov	Loughborough University, Loughborough, UK
18:45-19:05	Poster Award, MEMRISYS 2022, Closing Remarks Tsuyoshi Hasegawa Waseda University, Tokyo, Japan							